

**1. Material** Substrate GaAs (N Type)  
Epitaxial Layer GaAs (P/N Type)

**2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy

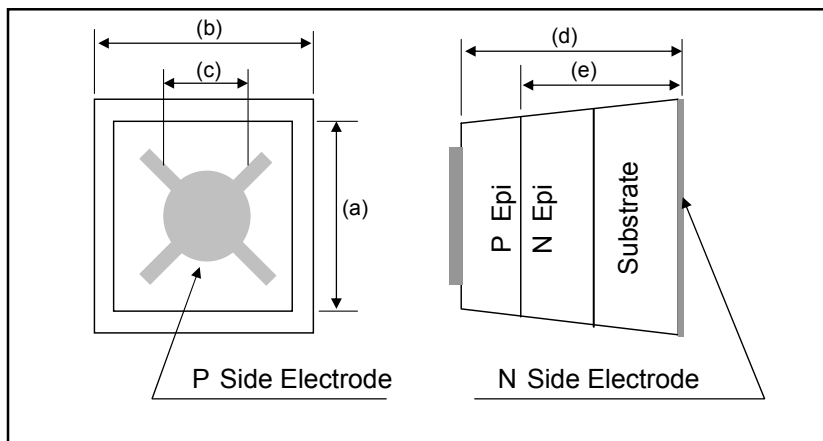
**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$			1.3	V	IF=20mA
	$V_{F(2)}$			1.57	V	IF=100mA
Reverse Voltage	$V_R$	8			V	IR=10uA
Power	$P_O$	8	11		mW	IF=100mA
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

(a) Emission Area	-----	10.5mil x 10.5mil
(b) Bottom Area	-----	11.5mil x 11.5mil
(c) Bonding Pad	-----	130um
(d) Chip Thickness	-----	7mil
(e) Junction Height	-----	4.7mil



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